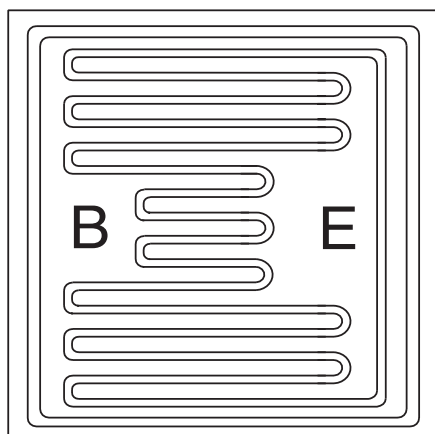


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	40 x 40 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	7.9 x 8.7 MILS
Emitter Bonding Pad Area	9.0 x 14 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

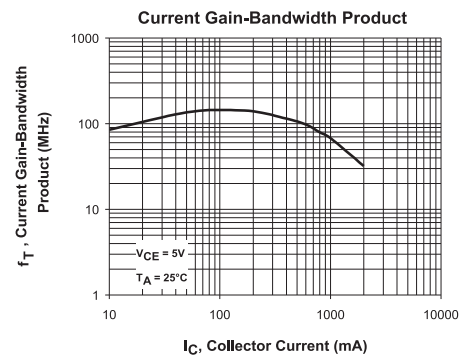
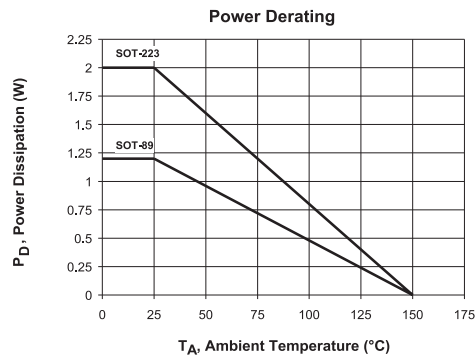
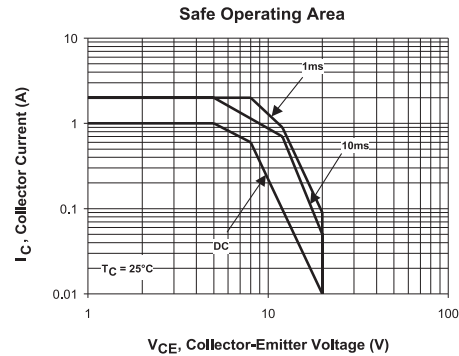
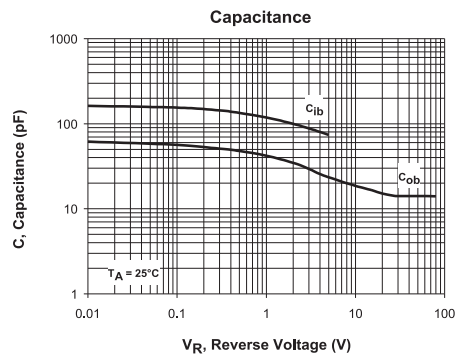
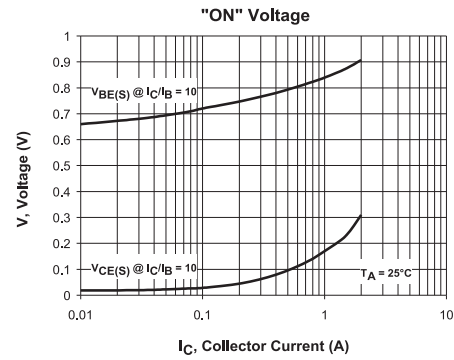
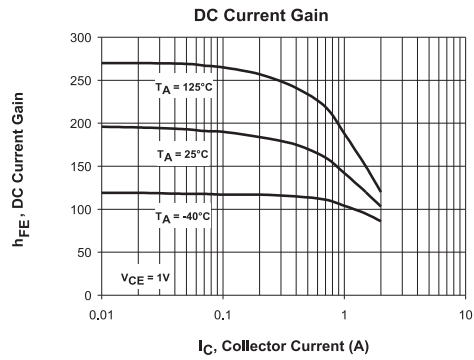
7,070

**PRINCIPAL DEVICE TYPES**

CBCP69  
CBCX69  
CZT751  
MPS750  
MPS751

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centrasemi.com](http://www.centrasemi.com)

R2 (1-August 2002)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

R2 (1-August 2002)